

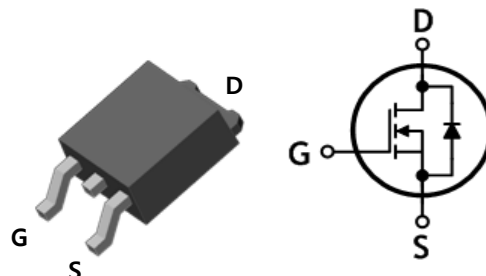
N-Channel Super Junction MOSFET

Features

- Drain-Source voltage: $V_{DS}=700V$ (@ $T_J=150^{\circ}C$)
- Low drain-source On resistance: $R_{DS(on)}=0.38\Omega$ (Max.)
- Ultra low gate charge: $Q_g=17.5nC$ (Typ.)
- RoHS compliant and Halogen free device
- 100% avalanche tested

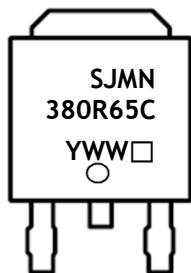
Ordering Information

Part Number	Marking	Package
SJMN380R65CD	SJMN380R65C	TO-252



TO-252

Marking Information



Column 1, 2: Device Code
 Column 3: Production Information
 e.g.) YWW□
 -. YWW: Date Code (year, week)
 -. □: Factory Management Code

Absolute maximum ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	650	V
Gate-source voltage	V_{GSS}	± 30	V
Drain current (DC) (Note 1)	I_D	$T_C=25^{\circ}C$	11
		$T_C=100^{\circ}C$	7
Drain current (Pulsed) (Note 1)	I_{DM}	44	A
Single pulsed avalanche energy (Note 2)	E_{AS}	10	mJ
Single avalanche current (Note 2)	I_{AS}	2	A
MOSFET dv/dt ruggedness ($V_{DS} \leq 400V$)	dv/dt	50	V/ns
Diode dv/dt ruggedness ($I_{SD} \leq I_D$, $V_{DS} \leq 400V$)	dv/dt	15	V/ns
Power dissipation	P_D	75	W
Junction temperature	T_J	150	$^{\circ}C$
Storage temperature range	T_{stg}	-55~150	$^{\circ}C$

Thermal Characteristics

Characteristic	Symbol	Rating	Unit
Thermal resistance, junction to case	$R_{th(j-c)}$	Max. 1.67	°C/W
Thermal resistance, junction to ambient	$R_{th(j-a)}$	Max. 62.5	

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	$I_D=1\text{mA}$, $V_{GS}=0$	650	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$I_D=0.8\text{mA}$, $V_{DS}=V_{GS}$	2.5	-	4.5	V
Drain-source cut-off current	I_{DSS}	$V_{DS}=650\text{V}$, $V_{GS}=0\text{V}$	-	-	1	uA
		$V_{DS}=650\text{V}$, $T_J=125^\circ\text{C}$	-	-	100	uA
Gate leakage current	I_{GSS}	$V_{DS}=0\text{V}$, $V_{GS}=\pm 30\text{V}$	-	-	± 100	nA
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=4\text{A}$	-	0.3	0.38	Ω
Internal gate resistance	R_g	$f=1\text{MHz}$, Open drain	-	1.1	-	Ω
Input capacitance (Note 3, 4)	C_{iss}	$V_{DS}=25\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	-	708	-	pF
Output capacitance (Note 3, 4)	C_{oss}		-	1120	-	
Reverse transfer capacitance (Note 3, 4)	C_{rss}		-	40	-	
Turn-on delay time (Note 3, 4)	$t_{d(on)}$	$V_{DS}=350\text{V}$, $I_D=11\text{A}$, $R_G=25\Omega$	-	28	-	ns
Rise time (Note 3, 4)	t_r		-	43	-	
Turn-off delay time (Note 3, 4)	$t_{d(off)}$		-	56	-	
Fall time (Note 3, 4)	t_f		-	39	-	
Total gate charge (Note 3, 4)	Q_g	$V_{DS}=400\text{V}$, $V_{GS}=10\text{V}$, $I_D=7\text{A}$	-	17.5	-	nC
Gate-source charge (Note 3, 4)	Q_{gs}		-	7.5	-	
Gate-drain charge (Note 3, 4)	Q_{gd}		-	4.5	-	

Source-Drain Diode Ratings and Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	I_S	Integral reverse diode in the MOSFET	-	-	11	A
Source current (Pulsed)	I_{SM}		-	-	44	A
Forward voltage	V_{SD}	$V_{GS}=0\text{V}$, $I_S=4\text{A}$	-	-	1.2	V
Reverse recovery time (Note 3,4)	t_{rr}	$I_S=11\text{A}$, $V_{GS}=0\text{V}$, $dI_S/dt=100\text{A/us}$	-	282	-	ns
Reverse recovery charge (Note 3,4)	Q_{rr}		-	3.6	-	uC

Note:

1. Calculated continuous current based on maximum allowable junction temperature
2. $L=5\text{mH}$, $V_{DD}=50\text{V}$, Starting $T_J=25^\circ\text{C}$
3. Guaranteed by design, not subject to production testing
4. Pulse test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

Typical Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

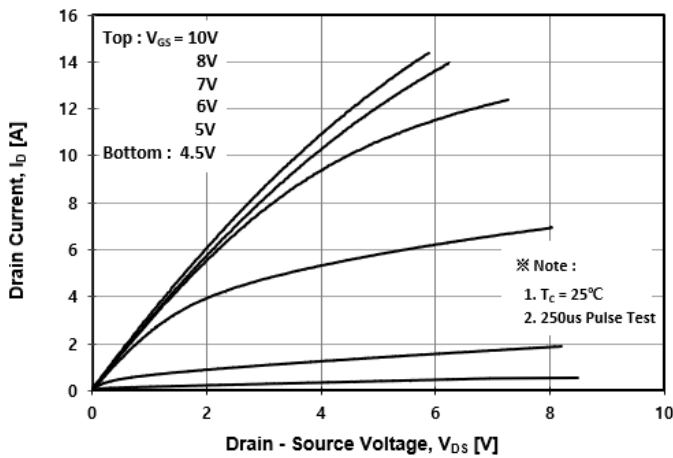


Fig. 2 Typical Transfer Characteristics

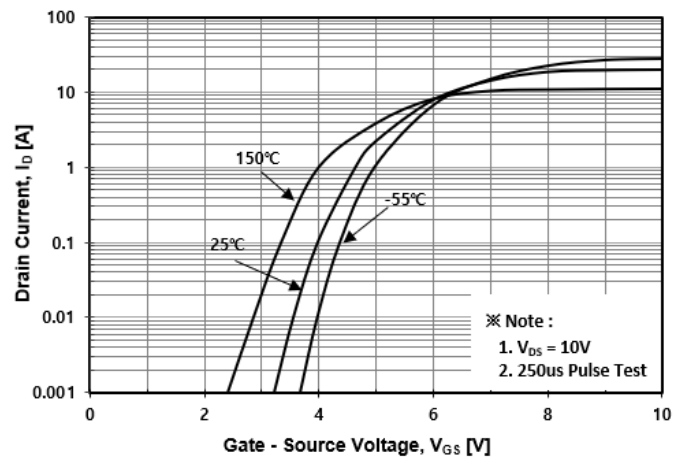


Fig. 3 On-Resistance Variation with Drain Current and Gate Voltage

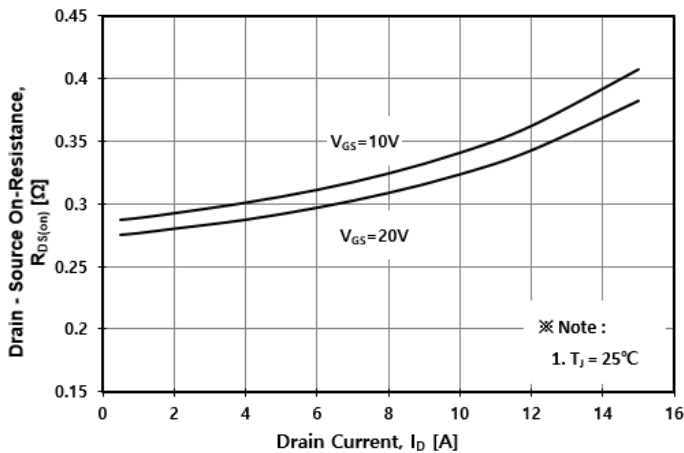


Fig. 4 Body Diode Forward Voltage Variation with Source Current

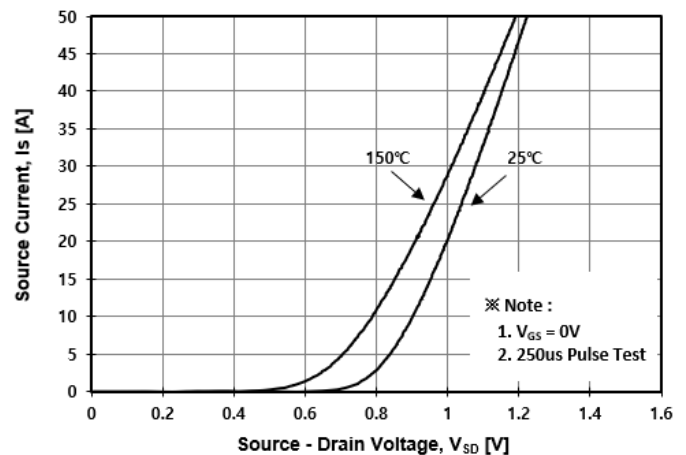


Fig. 5 Typical Capacitance Characteristics

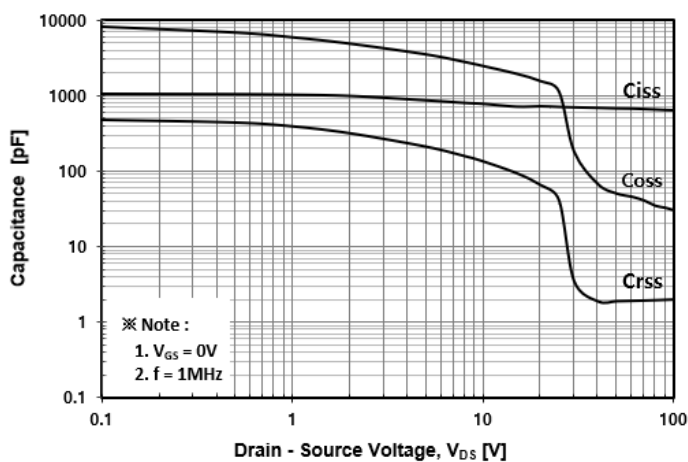
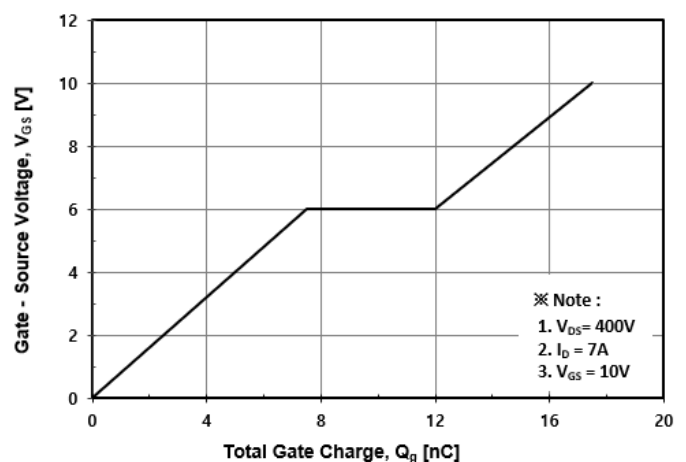


Fig. 6 Typical Total Gate Charge Characteristics



Typical Electrical Characteristics Curves

Fig. 7 Breakdown Voltage Variation vs. Temperature

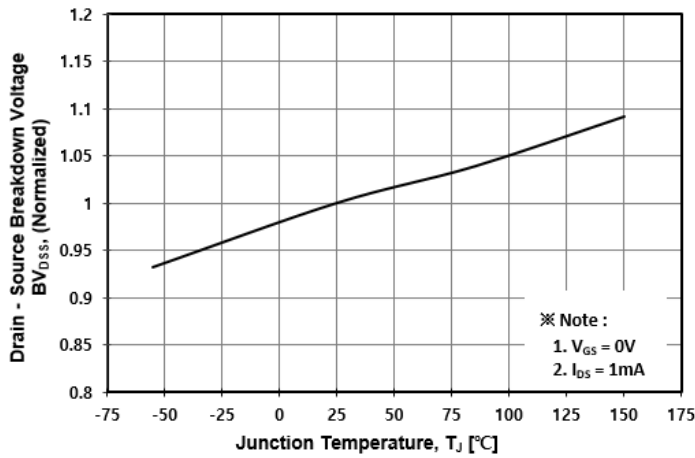


Fig. 8 On-Resistance Variation vs. Temperature

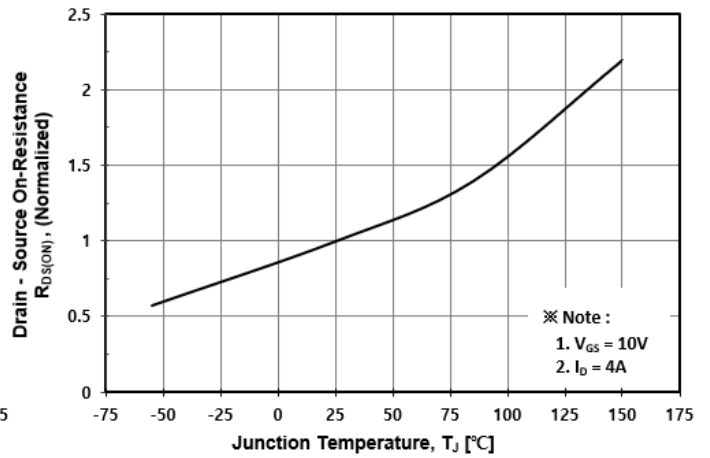


Fig. 9 Maximum Drain Current vs. Case Temperature

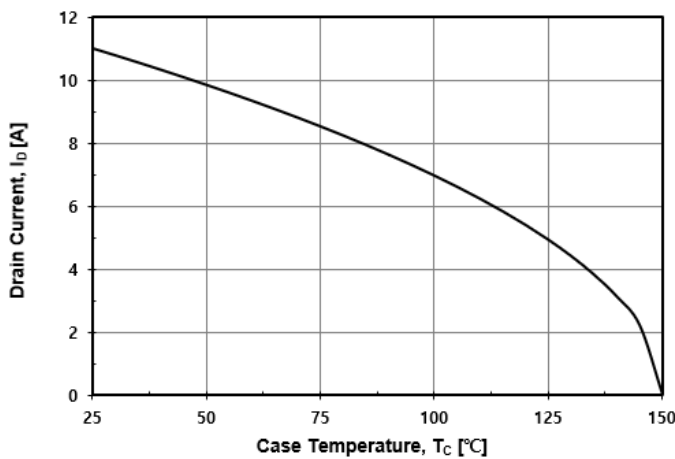


Fig. 10 Maximum Safe Operating Area

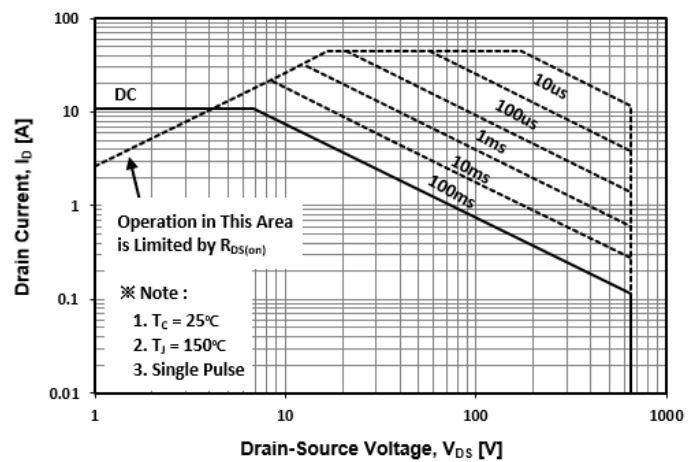


Fig. 11 Transient Thermal Impedance

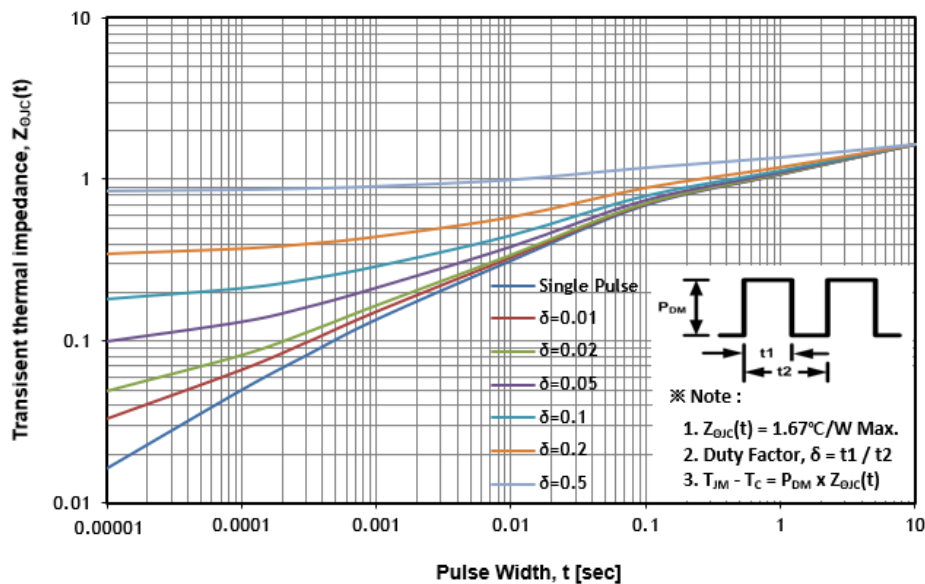


Fig. 12 Gate Charge Test Circuit & Waveform

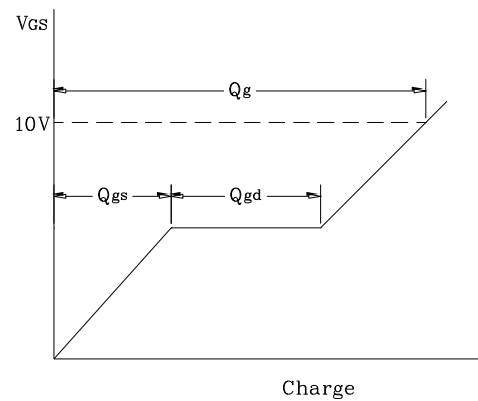
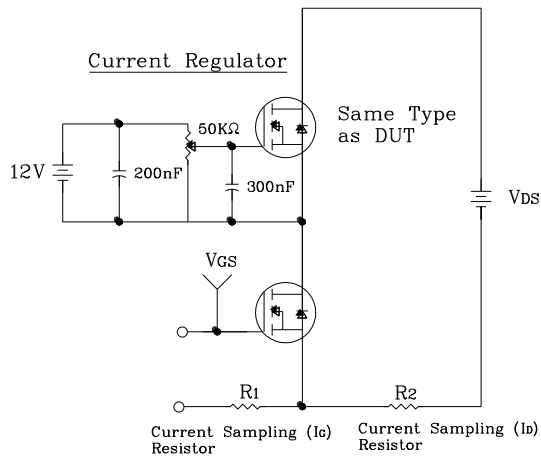


Fig. 13 Resistive Switching Test Circuit & Waveform

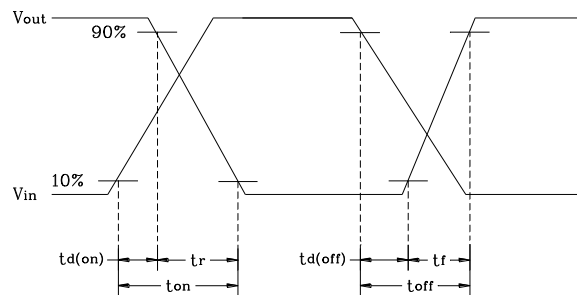
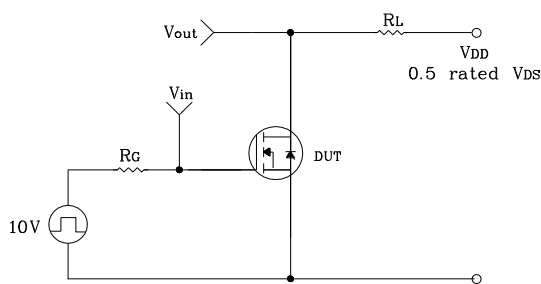


Fig. 14 E_{AS} Test Circuit & Waveform

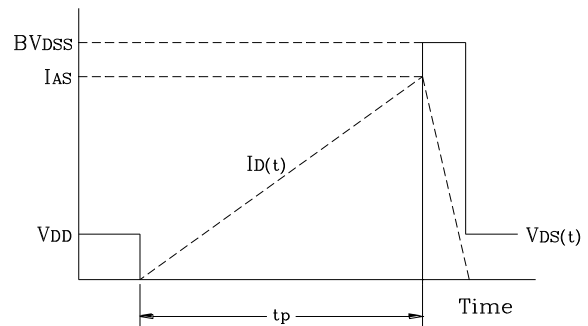
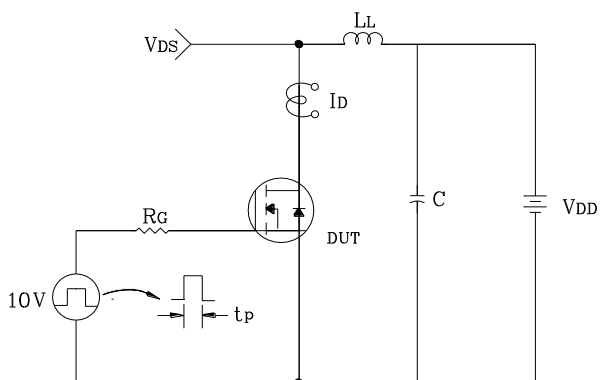
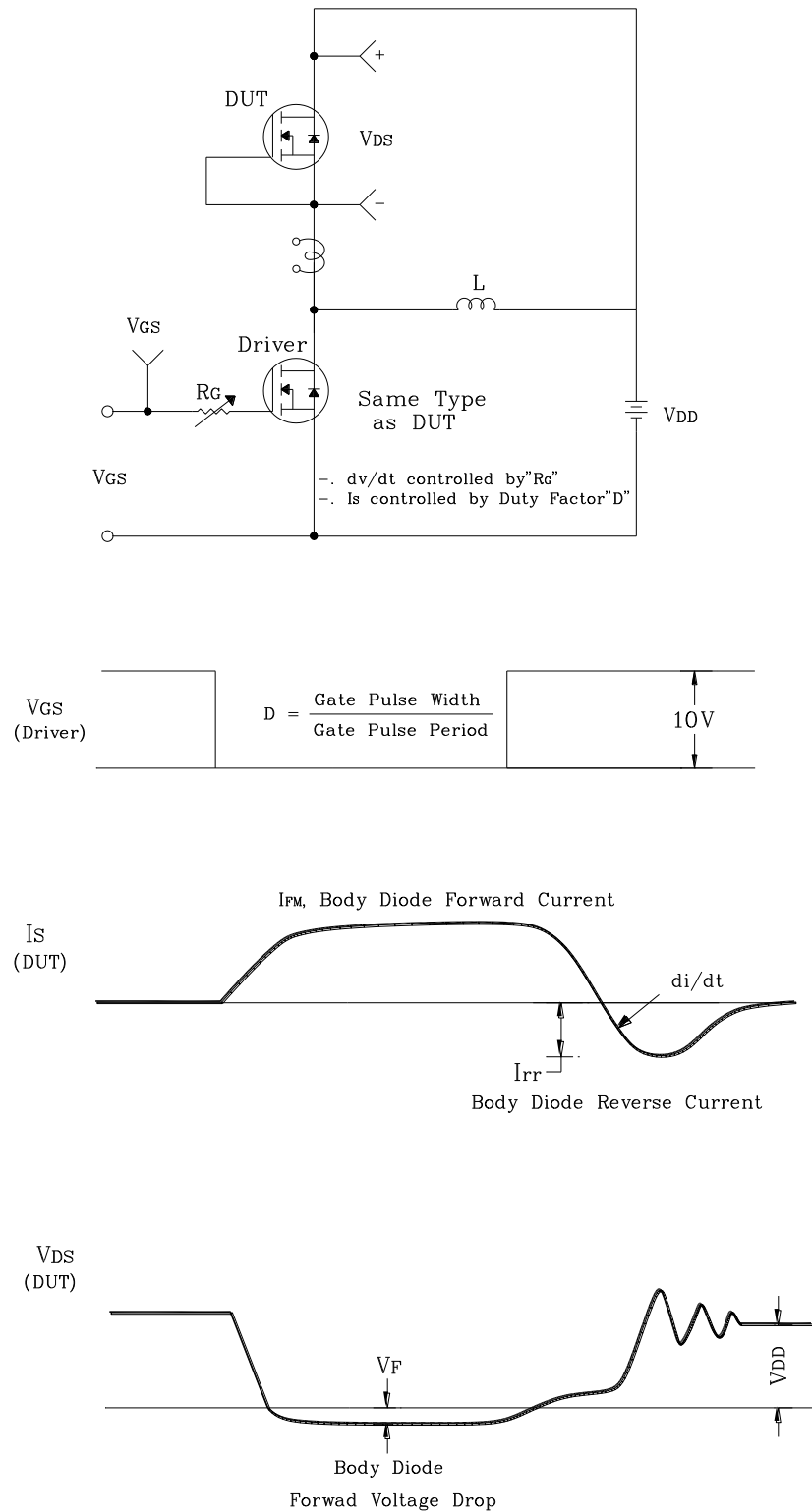
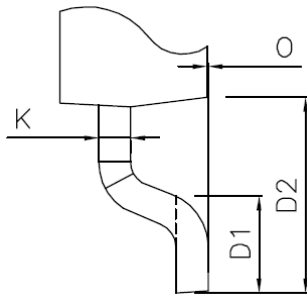
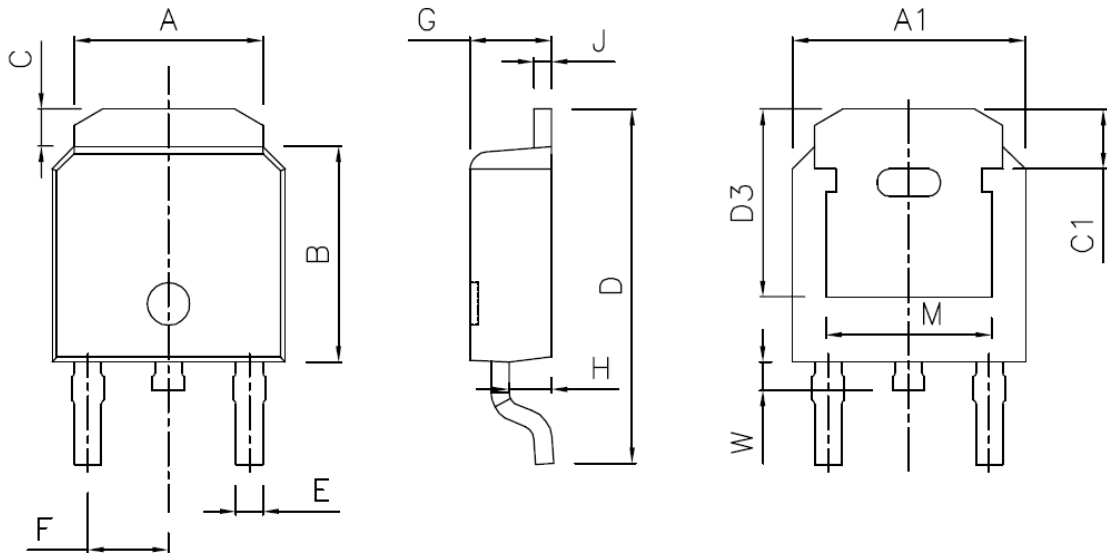


Fig. 15 Diode Reverse Recovery Time Test Circuit & Waveform



Package Outline Dimensions



SYMBOL	MILLIMETERS		
	MIN	NOR	MAX
A	5.03	5.34	5.64
A1	6.30	6.60	6.90
B	5.70	6.00	6.30
C	0.75	1.05	1.35
C1	1.021	1.321	1.621
D	9.65	9.95	10.25
D1	1.30	1.50	1.70
D2	2.70	2.90	3.10
D3	5.00	5.30	5.60
E	0.61	0.76	0.91
F	2.13	2.28	2.43
G	2.00	2.30	2.60
H	0.76	1.06	1.36
J	0.36	0.51	0.66
K	0.37	0.52	0.67
M	4.55	4.85	5.15
O	0.00	0.07	0.17
W	0.60	0.90	1.20

The AUK Corp. products are intended for the use as components in general electronic equipment (Office and communication equipment, measuring equipment, home appliance, etc.).

Please make sure that you consult with us before you use these AUK Corp. products in equipments which require high quality and / or reliability, and in equipments which could have major impact to the welfare of human life(atomic energy control, airplane, spaceship, transportation, combustion control, all types of safety device, etc.). AUK Corp. cannot accept liability to any damage which may occur in case these AUK Corp. products were used in the mentioned equipments without prior consultation with AUK Corp..

Specifications mentioned in this publication are subject to change without notice.